JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-223 Plastic-Encapsulate Transistors

PZTA42 TRANSISTOR (NPN)

SOT-223

1. BASE
2. COLLECTOR
3. EMITTER

FEATURES

- **High breakdown voltage**
- **Low collector-emitter saturation voltage**
- **Complementary type: PZTA92(PNP)**

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	0.5	A
P_C	Collector Power Dissipation	1	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

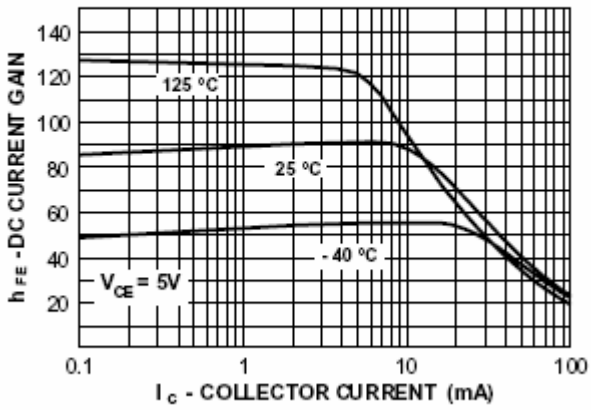
ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA,I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=200V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=6V,I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=10V,I_C=1mA	25			
	$h_{FE(2)}$	V_{CE}=10V,I_C=10mA	40			
	$h_{FE(3)}$	V_{CE}=10V,I_C=30mA	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=20mA,I_B=2mA			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=20mA,I_B=2mA			0.9	V
Transition frequency	f_T	V_{CE}=20V,I_C=10mA,f=100MHz	50			MHz
Collector output capacitance	C_{ob}	V_{CB}=20V,I_E=0,f=1MHz			3	pF

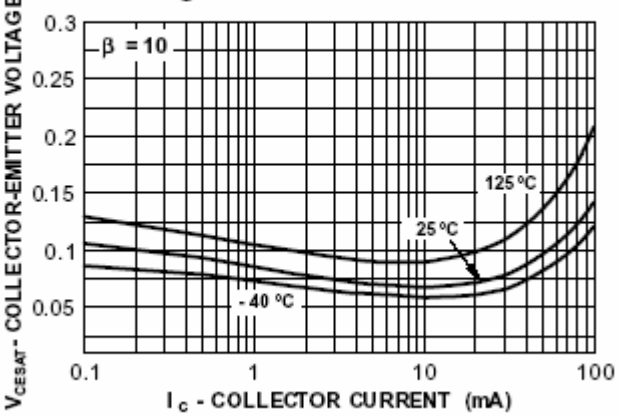
Typical Characteristics

PZTA42

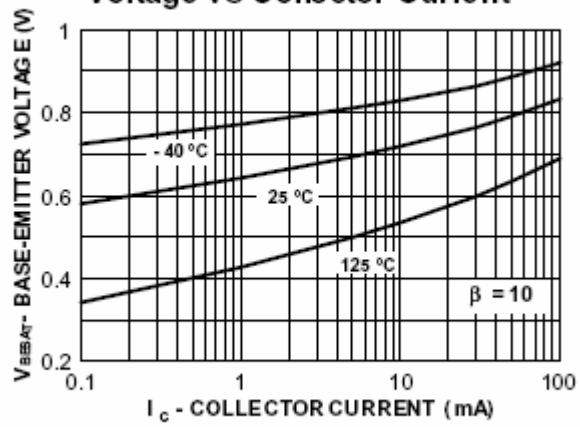
DC Current Gain
vs Collector Current



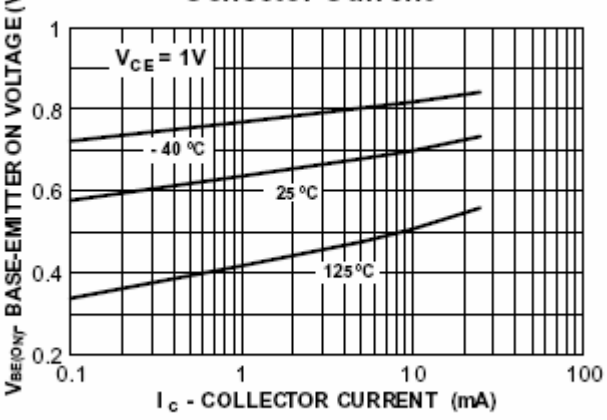
Collector-Emitter Saturation
Voltage vs Collector Current



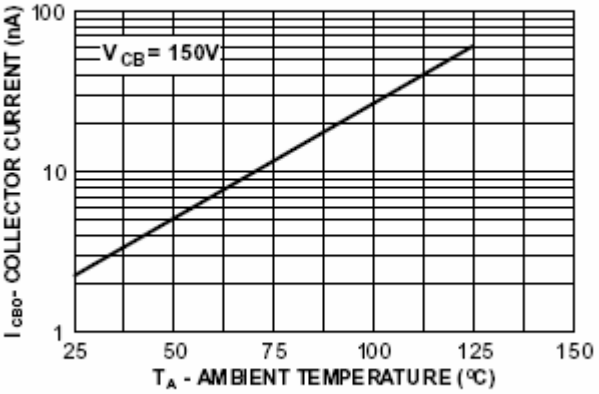
Base-Emitter Saturation
Voltage vs Collector Current



Base-Emitter ON Voltage vs
Collector Current



Collector-Cutoff Current
vs Ambient Temperature



Collector-Base and Emitter-Base
Capacitance vs Reverse Bias Voltage